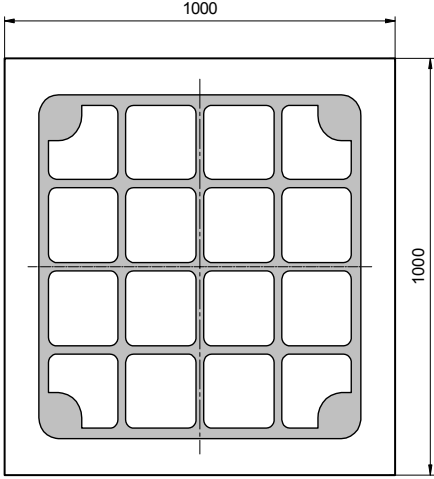


Radiation	Type	Technology	Electrodes
Deep red	solderable	AlGaAs/GaAs	N (cathode) up

 <p>PoC-05</p>	typ. dimensions (μm)	
	<u>typ. thickness</u> 260 (± 20) μm	
	<u>cathode</u> gold alloy, 1.5 μm	
	<u>anode</u> gold alloy, 0.5 μm	

Optical and Electrical Characteristics

$T_{\text{amb}} = 25^\circ\text{C}$, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20 \text{ mA}$	V_F		1.7	2.0	V
Forward voltage	$I_F = 300 \text{ mA}$	V_F		2.0	2.4	V
Reverse voltage	$I_R = 100 \mu\text{A}$	V_R	5			V
Radiant power	$I_F = 20 \text{ mA}$	Φ_e	0.75	1.0		mW
Radiant power ¹	$I_F = 300 \text{ mA}$	Φ_e	18	24		mW
Peak wavelength	$I_F = 300 \text{ mA}$	λ_p	685	700	710	nm
Spectral bandwidth at 50%	$I_F = 300 \text{ mA}$	$\Delta\lambda_{0.5}$		40		nm
Switching time	$I_F = 100 \text{ mA}$	t_r, t_f		40/30		ns

¹Measured on bare chip on TO-18 header with *EPIGAP* equipment

Labeling

Type	Lot N°	$\Phi_e(\text{typ})$ [mW]	$V_F(\text{typ})$ [V]	Quantity
ELC-685-21-15				

Packing: Chips on adhesive film with wire-bond side on top